/ Descriptions

U09 ṂṂ Ł ⁄ ᵍ⁀ ‖ ㄱ
Schottky Barrier Diode in a R-6 Plastic Package.

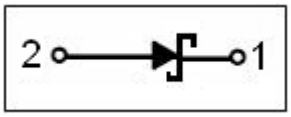
/ Features

Rs P RV ⁄ ᵍ Ṫ̊ Ḥ* ᵇ я ∪ ı Ḥ ı ǟ ↄ ̃ ' ظ Φ ㇋ ᗡ ㇄ □ ᵛ533 ɬ ı ƍ ᶿ گ ΐ ' ت Ẓ ɾ ₩ Ã HVG ΐ ㄒ ز ˙ °63NY
Trench MOS Schottky technology, Low forward voltage drop, low power losses, High efficiency operation, TJ ≤200 °C max. in solar bypass mode application, ESD ability to achieve ±30KV.

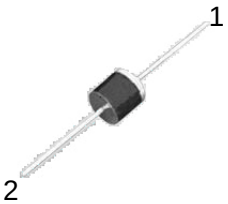
/ Applications

ᵹ ᶿ گ ΐ ɔ – ì ɻ ¨ ₳ OBJ ' ت ʒ ï‾ ‖ ㄱ ↄ ᵼ ' ڴ ᴪ ʜ ı Ã ʜ ɔ ◊ ı ㇒ ㇍ ‖ ㄱ ı RU0lq j ‾ ‖ ㄱ ı GF0GF ᶎ Ω ʜ ⊃ ɔ – ɾ ᵇ ʒ ï
For use in solar cell junction box as a bypass diode for protection, high frequency inverters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

/ Equivalent Circuit



/ Pinning



PIN1 χ Cathode PIN 2 χ Anode

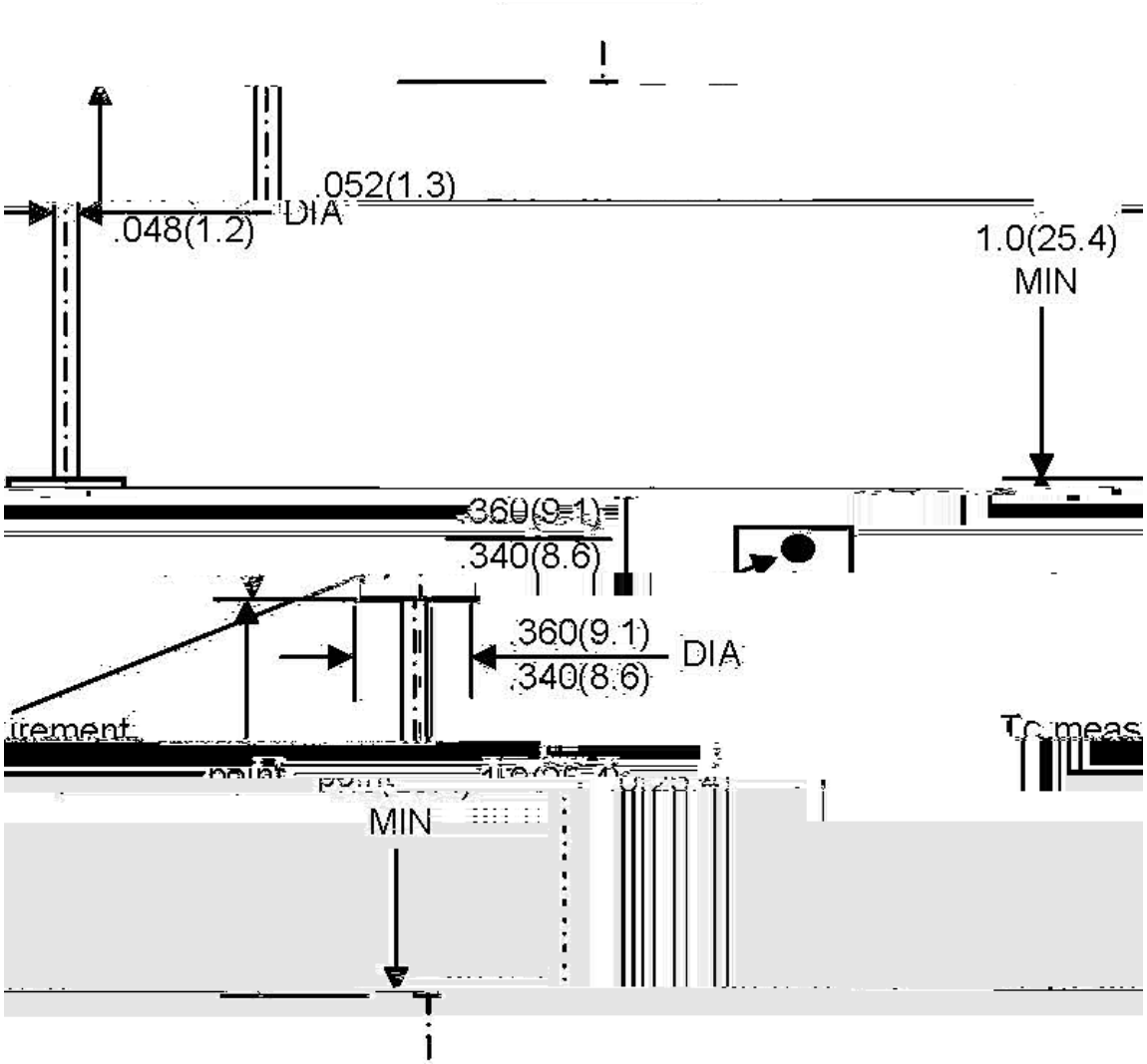
/ h_{FE} Classifications & Marking

ð м ヿ ب ˝ See Marking Instructions.

v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ɥ Unit

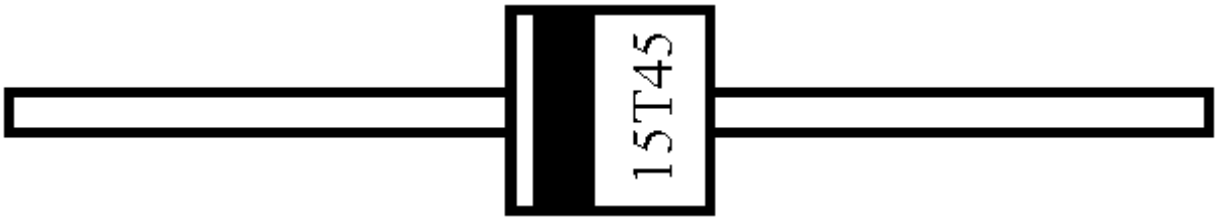
/ Package Dimensions

R-6



Dimensions in inches and (millimeters)

/ Marking Instructions



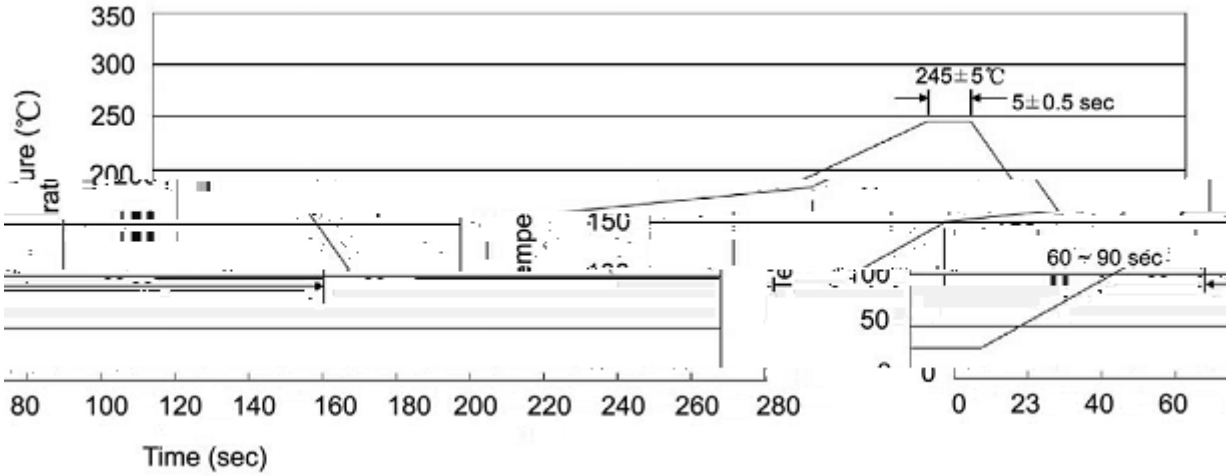
ب ″ χ

48W78 χ ᵻ ʒ ᴺ Ґ

Note:

48W78 χ Product Type Code.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı `H ژ 60 Ḱ 90sec;

Note:

1.Preheating:25~150 ł